

JAN 03 2005

COMPLETED

DEP # REF
Room 307

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Masahiro SAKURADA et al.

Application No.: 10/500,580

Filed: July 1, 2004

For: AN SOI WAFER AND A METHOD FOR PRODUCING AN SOI WAFER

ATTN:

Refund Section
Accounting Div.
Office of Finance

Docket No.: 120222

REQUEST FOR REFUND TO DEPOSIT ACCOUNT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Attached hereto is a copy of a Monthly Statement of Deposit Account (dated November, 2004) showing a charge of \$290.00 related to the above-referenced application. This charge is marked with Fee Code 1616, which is the Patent Office Fee for multiple dependent claims. However, a preliminary amendment was filed with the original application on July 1, 2004 to amend the multiple dependent claims. Attached hereto is a duplicate copy of the preliminary amendment as filed, as well as a copy of the date-stamped receipt acknowledging receipt of the preliminary amendment on July 1, 2004.

Accordingly, it is respectfully requested that this charge be re-credited to Deposit Account No. 15-0461 and that the Patent Office acknowledge this credit in writing.

Respectfully submitted,

William P. Berridge

Registration No. 30,024

Eric D. Morehouse

Registration No. 38,565

WPB:EDM/dmr

Date: January 3, 2005

OLIFF & BERRIDGE, PLC
P.O. Box 19928
Alexandria, Virginia 22320
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DEPOSIT ACCOUNT USE
AUTHORIZATION
Please grant any extension
necessary for entry;

OTPE JC98
JAN 03 2005

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TO: SAC, NEW YORK

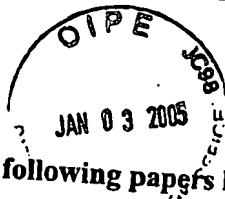


DT07 Rec'd PET/PTO 01 JUL 2004
PTO RECEIPT FOR FILING OF PAPER

The following papers have been filed:

PCT Trans; CK 155713 (\$920); Prelim; Transl PCT Req; 35 pp spec/6clms/abstract; 9 pp dwngs (Figs. 1a-9); Dec; Assgn trans; CK 155714 (\$40); Assgn; IDS; Pto 1449 w/5 Refs, 5 abstracts, 5 transl & srch rpt

Name of Applicant:	Masahiro SAKURADA; Nobuaki MITAMURA; Izumi FUSEGAWA; Tomohiko OHTA
Serial No.:	New U.S. Patent Application 10/500580
Atty. File No.:	120222
Title (New Cases):	AN SOI WAFER AND A METHOD FOR PRODUCING AN SOI WAFER
Sender's Initials:	WPB/mlo
ASSIGNEE:	SHIN-ETSU HANDOTAI CO., LTD.



PTO RECEIPT FOR FILING OF PAPERS

The following papers have been filed:

PCT Trans; CK 155713 (\$920); Prelim; Transl PCT Req; 35 pp spec/6clms/abstract; 9 pp dwngs (Figs. 1a-9); Dec; Assgn trans; CK 155714 (\$40); Assgn; IDS; Pto 1449 w/5 Refs, 5 abstracts, 5 transl & srch rpt

Name of Applicant: Masahiro SAKURADA; Nobuaki MITAMURA; Izumi FUSEGAWA; Tomohiko OHTA

Serial No.: New U.S. Patent Application

Atty. File No.: 120222

Title (New Cases): AN SOI WAFER AND A METHOD FOR PRODUCING AN SOI WAFER

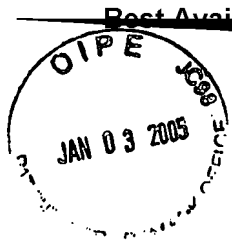
Sender's Initials: WPB/mlo

11/25
NEW APPLICATION



PATENT OFFICE DATE STAMP

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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Masahiro SAKURADA et al.

Application No.: New U.S. National Stage of
PCT/JP03/13645

Filed: July 1, 2004

Docket No.: 120222

For: AN SOI WAFER AND A METHOD FOR PRODUCING AN SOI WAFER

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Please consider the following:

Amendments to the Specification;

Amendments to the Claims as reflected in the listing of claims;

Remarks.

New U.S. National Stage of PCT/JP03/13645

Amendments to the Specification

Please replace the title as follows:

~~SOI WAFER AND METHOD FOR MANUFACTURING SOI WAFER~~

AN SOI WAFER AND A METHOD FOR PRODUCING AN SOI WAFER

AMENDMENTS TO THE CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-13 are cancelled.

14. (New) An SOI wafer in which at least a silicon active layer is formed on a support substrate, wherein at least the silicon active layer consists of silicon single crystal grown by Chochralski method, which is occupied by N region outside OSF generated in a shape of a ring and has no defect region detected by Cu deposition method.
15. (New) The SOI wafer according to Claim 14, wherein a thickness of the silicon active layer is 200 nm or less.
16. (New) The SOI wafer according to claim 14, wherein the silicon active layer is formed by being bonded to the support substrate via an oxide film.
17. (New) The SOI wafer according to claim 15, wherein the silicon active layer is formed by being bonded to the support substrate via an oxide film.
18. (New) The SOI wafer according to claim 16, wherein a thickness of the oxide film is in the range from 2 nm to 3000 nm.
19. (New) The SOI wafer according to claim 17, wherein a thickness of the oxide film is in the range from 2 nm to 3000 nm.
20. (New) The SOI wafer according to claim 14, wherein the SOI wafer is produced by

ion implantation delamination method.

21. (New) The SOI wafer according to claim 15, wherein the SOI wafer is produced by ion implantation delamination method.

22. (New) The SOI wafer according to claim 16, wherein the SOI wafer is produced by ion implantation delamination method.

23. (New) The SOI wafer according to claim 17, wherein the SOI wafer is produced by ion implantation delamination method.

24. (New) The SOI wafer according to claim 18, wherein the SOI wafer is produced by ion implantation delamination method.

25. (New) The SOI wafer according to claim 19, wherein the SOI wafer is produced by ion implantation delamination method.

26. (New) A method for producing an SOI wafer comprising steps of, in a bond wafer that is to be a silicon active layer and a base wafer that is to be a support substrate, implanting hydrogen ions, rare gas ions or mixture gas ions of these gases from a surface of the bond wafer to form an ion-implanted layer inside the bond wafer, bonding the surface of the ion-implanted side of the bond wafer and a surface of the base wafer via an oxide film or directly, and delaminating a part of the bond wafer at the ion-implanted layer by heat treatment to form an SOI wafer, wherein a silicon wafer consisting of silicon single crystal grown by Chochralski method, which is occupied by N region outside OSF generated in a shape of a

New U.S. National Stage of PCT/JP03/13645

ring and has no defect region detected by Cu deposition method, is used as the bond wafer.

REMARKS

Claims 14-26 are pending in this application. By this Amendment, the title is amended and claims 1-13 are cancelled. Claims 14-26 are new.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,

William P. Berridge
Registration No. 30,024

Thomas J. Pardini
Registration No. 30,411

WPB:TJP/mlo

Date: July 1, 2004

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